

# **Notice of References Cited**

Application No. **08/339,977**

Applicant(s)

**Daberko et al.**

Examiner

**John Michael Grover**

Group Art Unit

**2308**

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## **U.S. PATENT DOCUMENTS**

	DOCUMENT NO.	DATE	NAME	CLASS	SUBCLASS
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B	5,357,595	10/94	Sudoh et al.	395	2.24
C	5,499,316	3/96	Sudoh et al.	395	2.79
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N	DE 4,207 447A1	9/16/93	GERMANY	Holzer	G10L	5/04
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## **NON-PATENT DOCUMENTS**

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V	Masuoka, "TECHNOLOGY TREND OF FLASH - EEPROM", IEEE Symposium on VLSI Technology Digests of Technical Papers, 1992.	4/92
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